

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Martin Hausner
Serial No.: Unknown (National Phase of International Application
PCT/EP03/09052)
Filed: February 11, 2005 (Priority Date Claimed August 14,
2002)
Examiner: Unknown
Group Art Unit: Unknown
Confirmation No.: Unknown
Title: **METHOD FOR SELECTIVELY REMOVING MATERIAL
FROM THE SURFACE OF A SUBSTRATE, MASKING
MATERIAL FOR A WAFER, AND WAFER WITH MASKING
MATERIAL**
Our Ref. No.: BEET-09

Cincinnati, Ohio 45202

February 11, 2005

Mail Stop PCT
Commissioner for Patents
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Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of candor and good faith imposed by 37
C.F.R. §1.56 and means of complying therewith according to 37 C.F.R. §§1.97
and 1.98, the references listed on the attached Form PTO-1449 are called to the

attention of the United States Patent and Trademark Office in connection with the above-identified patent application. Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been waived, copies of only the foreign cited references and/or other documents are enclosed herewith.


No representation is made that the cited art is the only art or that the cited art represents the best art.

The Examiner is urged to consider all of the cited documents and to make an independent evaluation of the teachings and materiality of each.

No fees are believed to be due. However, if any additional fees are necessary to complete this communication, please apply them to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				APPLICANT Martin Hausner									
				FILING DATE February 11, 2005		GROUP Unknown							
U.S. PATENT DOCUMENTS													
EXAMINER INITIAL		PATENT NUMBER				ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE			
	A.A	6	0	7	4	9	4	6	06/2000	Ouellet et al.	438	689	02/1997
	A.B	6	4	5	8	6	1	5	10/2002	Fedder et al.	438	50	09/1999
	A.C												
	A.D												
	A.E												
	A.F												
	A.G												
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	A.I												
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FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS													
		DOCUMENT NUMBER				PUBLICATION DATE		COUNTRY OR PATENT OFFICE		CLASS	SUBCLASS	TRANSLATION (YES/NO)	
	A.L	DE 196 41 288 A1				04/1998		Germany		C23F	4/00	No	
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OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)													
	A.R	Ayon et al., <u>Anisotropic silicon trenches 300-500 um deep employing time multiplexed deep etching (TMDE)</u> , Sensors and Actuators A, Vol. 91, 2001, pp. 381-385											
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	B.R	IBM Corp., <u>IBM Technical Disclosure Bulletin</u> , Vol. 34, No. 5, October 1991, pp. 368-370
	B.S	EPO, <u>International Search Report</u> , PCT/EP03/09052, May 18, 2004 (14 pages)
	B.T	Kong et al., <u>Reactive Ion Etching of SiC Using C2F6/02 Inductively Coupled Plasma</u> , Journal of Electronic Materials, Vol. 31, No. 3, March 2002, pp. 209-213

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C.R	A. J. Perry and R. W. Boswell, <u>Fast anisotropic etching of silicon in an inductively coupled plasma reactor</u> , Applied Physics Letters, American Institute of Physics, New York, Vol. 55, No. 2, July 10, 1989, pp. 148-150
C.S	Rakhshandehroo et al., <u>Dry etching of Si field emitters and high aspect ratio resonators using an inductively coupled plasma source</u> , Journal of Vacuum Science and Technology: Part B, American Institute of Physics, New York, Vol. 16, No. 5, Sept./Oct. 1998, pp. 2849-2854
C.T	Song et al., <u>Method Of Through-Etching Substrate</u> , United States Patent Application Publication No. 2003/0162402A1, Publication Date of August 28, 2003 (14 pages)

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D.R	Tanaka et al., <u>Deep reactive ion etching of silicon carbide</u> , Journal of Vacuum Science and Technology B, Vol. 19, No. 6, Nov./Dec. 2001, pp. 2173-2176
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D.T	Jason W. Weigold, <u>Design and Fabrication of Submicrometer, Single Crystal Si Accelerometer</u> , Journal of Microelectromechanical Systems, IEEE Inc., New York, Vol. 10, No. 4, December 2001, pp. 518-524

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	E.R	Xiao et al., <u>Silicon micro-accelerometer with mg resolution, high linearity and large frequency bandwidth fabricated with two mask bulk process</u> , Sensors and Actuators A, Vol. 77, 1999, pp. 113-119
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